



Docket No.: M1071.1392

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re Patent Application of:
Yutaka Takeshima, et al.

Dated: February 22, 2003

Application No.: 09/916,804

Group Art Unit: 1762

Filed: July 27, 2001

Examiner: M. Barr

For: METHOD OF PRODUCING COMPLEX
OXIDE THIN-FILM AND
PRODUCTION APPARATUS

Assistant Commissioner for Patents
Washington, D.C. 20231

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MBA
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AMENDMENT

This is a response to the Advisory Action mailed January 28, 2003 in the above-identified application. Reconsideration of the application is respectfully requested.

FEE CALCULATION

There are no additional fees required.

	No. Claims After Amendment		Highest No. Previously Paid For		Extra Present		Rate	Additional Fee
Total	14	MINUS	*20	=		X		\$
Indep.	1	MINUS	**3	=		X		\$
First presentation of multiple dependent claim(s)						X		\$
TOTAL								\$ -0-

* not less than 20

** not less than 3

In the event the actual fee is greater than the payment submitted or is inadvertently not enclosed or if any additional fee during the prosecution of this application is not paid, the Patent Office is authorized to charge the underpayment to Deposit Account No. 50-2215.

CONTINGENT EXTENSION REQUEST

If this communication is filed after the shortened statutory time period had elapsed and no separate Petition is enclosed, the Commissioner of Patents and Trademarks is petitioned, under 37 C.F.R. § 1.136(a), to extend the time for filing a response to the outstanding Office Action by the number of months which will avoid abandonment under 37 C.F.R. § 1.135. The fee under 37 C.F.R. § 1.17 should be charged to our Deposit Account No. 50-2215.

AMENDMENTS

Please amend claim 1 pursuant to 37 C.F.R. § 1.121(c)(1)(i) as set forth in the "clean" version set forth below. Entry is respectfully requested. A version marked up to show the changes being made is attached hereto as Appendix A. ✓

The optional complete set of "clean" claims pursuant to 37 CFR 1.121(c)(3) is attached hereto as Appendix B.

1. A method of producing a complex oxide thin-film comprising the steps of:
 - (a) providing a metal compound solution comprising at least two metal compounds dissolved in a solvent;
 - (b) atomizing the metal compound solution in a two-fluid nozzle having a discharge end in a film-forming chamber, and directly introducing the atomized solution into the film-forming chamber in which the pressure is about 100 Torr or lower and having a substrate therein, and
 - (c) forming a complex oxide thin-film on a substrate in the film-forming chamber at a temperature equal to or higher than the boiling point of the solvent.